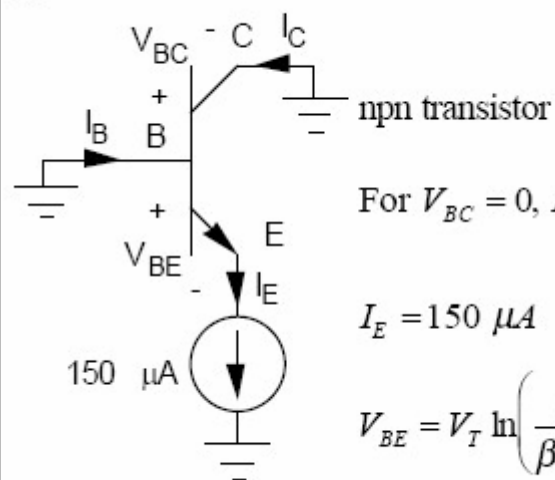


5.7

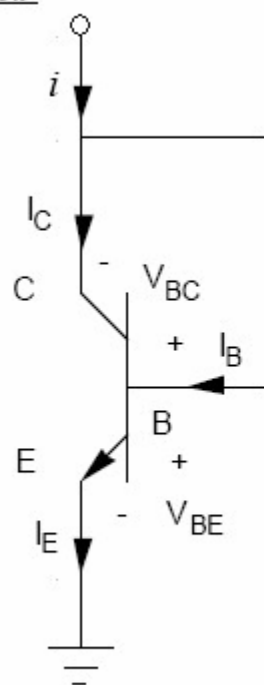


$$\text{For } V_{BC} = 0, I_E = I_S \left(1 + \frac{1}{\beta_F} \right) \left[\exp \left(\frac{V_{BE}}{V_T} \right) - 1 \right] \quad | \quad I_B = \frac{I_E}{\beta_F + 1} \quad | \quad I_C = \beta_F I_B$$

$$I_E = 150 \mu A \quad | \quad I_B = \frac{150 \mu A}{101} = 1.49 \mu A \quad | \quad I_C = \frac{100}{101} 150 \mu A = 149 \mu A$$

$$V_{BE} = V_T \ln \left(\frac{\beta_F}{\beta_F + 1} \frac{I_E}{I_S} + 1 \right) = 0.025 V \ln \left(\frac{100}{101} \frac{150 \mu A}{2 fA} + 1 \right) = 0.626 V$$

5.9



Remember diode equation is :

$$i_D = I_S \left[\exp \left(\frac{v_D}{nV_T} \right) - 1 \right]$$

Using $v_{BC} = 0$ in following transport model equation

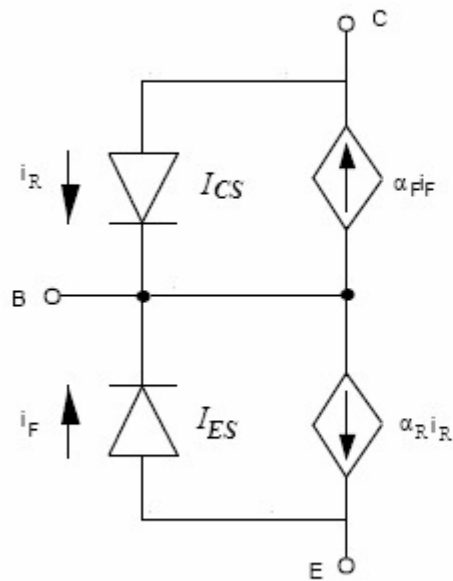
$$i_E = I_S \left[\exp \left(\frac{v_{BE}}{V_T} \right) - \exp \left(\frac{v_{BC}}{V_T} \right) \right] + \frac{I_S}{\beta_F} \left[\exp \left(\frac{v_{BE}}{V_T} \right) - 1 \right]$$

and recognizing that $i = i_C + i_B = i_E$:

$$i = i_E = I_S \left(1 + \frac{1}{\beta_F} \right) \left[\exp \left(\frac{v_{BE}}{V_T} \right) - 1 \right], \text{ and the reverse saturation current}$$

$$\text{of the diode connected transistor is } I_S' = I_S \left(1 + \frac{1}{\beta_F} \right) = (2 fA) \left(1 + \frac{1}{100} \right) = 2.02 fA$$

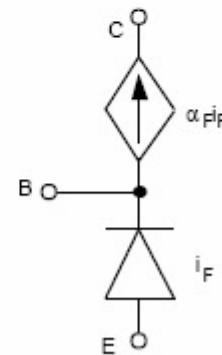
5.29



After substituting $V_{CB} = 0$ on following equations,

$$i_F = I_{ES} \left[\exp\left(\frac{v_{EB}}{V_T}\right) - 1 \right] \quad i_R = I_{CS} \left[\exp\left(\frac{v_{CB}}{V_T}\right) - 1 \right]$$

the simplified version of Ebers model is shown at below :



5.39

$$\text{At } I_C = 5 \text{ mA and } V_{CE} = 5 \text{ V, } I_B = 60 \mu\text{A}: \beta_F = \frac{I_C}{I_B} = \frac{5 \text{ mA}}{60 \mu\text{A}} = 83.3$$

$$\text{At } I_C = 7 \text{ mA and } V_{CE} = 7.5 \text{ V, } I_B = 80 \mu\text{A}: \beta_F = \frac{I_C}{I_B} = \frac{7 \text{ mA}}{80 \mu\text{A}} = 87.5$$

$$\text{At } I_C = 10 \text{ mA and } V_{CE} = 14 \text{ V, } I_B = 100 \mu\text{A}: \beta_F = \frac{I_C}{I_B} = \frac{10 \text{ mA}}{100 \mu\text{A}} = 100$$

5.58

(a) pnp transistor with $V_{EB} = -3V$ and $V_{CB} = -3V$ is in *Cutoff*

Substituting V_{EB} , V_{CB} , β_F , β_R , and I_S in the following equations :

$$i_C = I_S \left[\exp\left(\frac{v_{EB}}{V_T}\right) - \exp\left(\frac{v_{CB}}{V_T}\right) \right] - \frac{I_S}{\beta_R} \left[\exp\left(\frac{v_{CB}}{V_T}\right) - 1 \right] \rightarrow I_C = + \frac{I_S}{\beta_R} = \frac{10^{-15} A}{2} = 0.5 \times 10^{-15} = 0.5 \text{ fA}$$

$$i_E = I_S \left[\exp\left(\frac{v_{EB}}{V_T}\right) - \exp\left(\frac{v_{CB}}{V_T}\right) \right] + \frac{I_S}{\beta_F} \left[\exp\left(\frac{v_{BE}}{V_T}\right) - 1 \right] \rightarrow I_E = - \frac{I_S}{\beta_F} = \frac{10^{-15} A}{75} = 13.3 \times 10^{-18} = 13.3 \text{ aA}$$

$$i_B = \frac{I_S}{\beta_F} \left[\exp\left(\frac{v_{EB}}{V_T}\right) - 1 \right] + \frac{I_S}{\beta_R} \left[\exp\left(\frac{v_{CB}}{V_T}\right) - 1 \right] \rightarrow I_B = -I_S \left(\frac{1}{\beta_F} + \frac{1}{\beta_R} \right) = 10^{-15} A \left(\frac{1}{75} + \frac{1}{2} \right) = 0.513 \times 10^{-15} = 0.513 \text{ fA}$$

(b) npn transistor with $V_{BE} = -5V$ and $V_{BC} = -5V$ is in *Cutoff*

Substituting V_{EB} , V_{CB} , β_F , β_R , and I_S in the following equations :

$$i_C = I_S \left[\exp\left(\frac{v_{BE}}{V_T}\right) - \exp\left(\frac{v_{BC}}{V_T}\right) \right] - \frac{I_S}{\beta_R} \left[\exp\left(\frac{v_{BC}}{V_T}\right) - 1 \right] \rightarrow I_C = + \frac{I_S}{\beta_R} = \frac{10^{-15} A}{2} = 0.5 \times 10^{-15} = 0.5 \text{ fA}$$

$$i_E = I_S \left[\exp\left(\frac{v_{BE}}{V_T}\right) - \exp\left(\frac{v_{BC}}{V_T}\right) \right] + \frac{I_S}{\beta_F} \left[\exp\left(\frac{v_{BE}}{V_T}\right) - 1 \right] \rightarrow I_E = - \frac{I_S}{\beta_F} = \frac{10^{-15} A}{75} = 13.3 \times 10^{-18} = 13.3 \text{ aA}$$

$$i_B = \frac{I_S}{\beta_F} \left[\exp\left(\frac{v_{BE}}{V_T}\right) - 1 \right] + \frac{I_S}{\beta_R} \left[\exp\left(\frac{v_{BC}}{V_T}\right) - 1 \right] \rightarrow I_B = -I_S \left(\frac{1}{\beta_F} + \frac{1}{\beta_R} \right) = 10^{-15} A \left(\frac{1}{75} + \frac{1}{2} \right) = 0.513 \times 10^{-15} = 0.513 \text{ fA}$$

The currents are the same as in part (a).

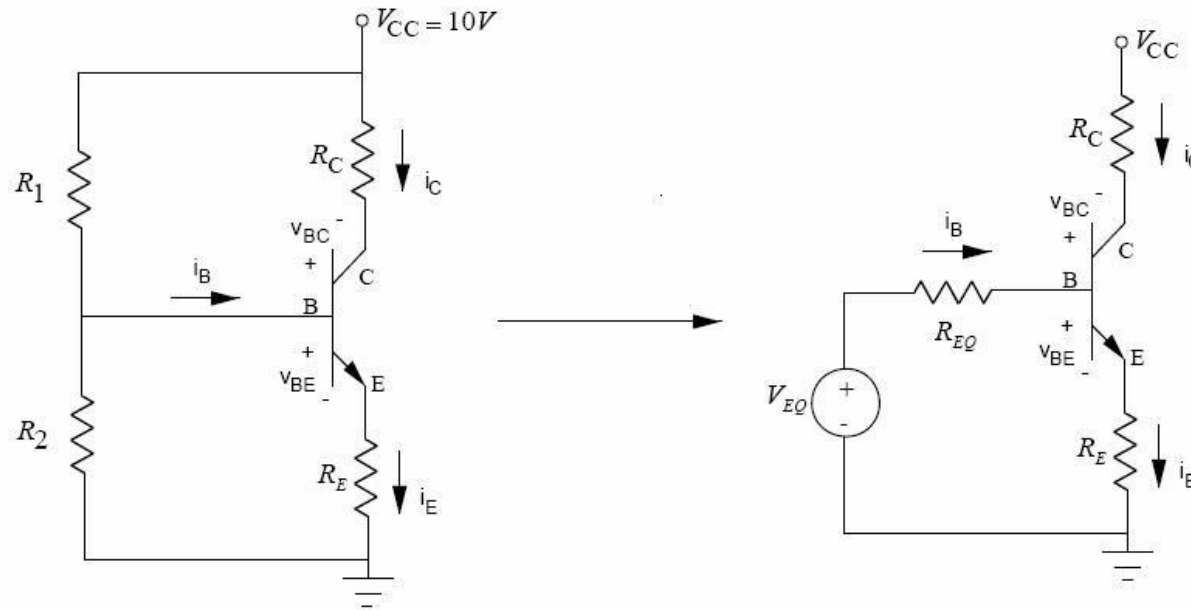
5.61

A pnp transistor with $V_{EB} = 0.7V$ and $V_{CB} = -0.7V \Rightarrow$ Forward - active region

$$\beta_F = \frac{I_C}{I_B} = \frac{2.5mA}{0.05mA} = 50$$

$$i_C = I_S \left[\exp\left(\frac{v_{EB}}{V_T}\right) - \exp\left(\frac{v_{CB}}{V_T}\right) \right] - \frac{I_S}{\beta_R} \left[\exp\left(\frac{v_{CB}}{V_T}\right) - 1 \right] \xrightarrow{\substack{\approx 0 \\ \left(I_S \exp\left(\frac{v_{EB}}{V_T}\right) \gg \frac{I_S}{\beta_R} \right)}} I_C = I_S \exp\left(\frac{V_{EB}}{V_T}\right) \xrightarrow{\substack{\approx 0}} I_S = \frac{2.5mA}{\exp\left(\frac{0.7V}{0.025V}\right)} = 1.73 fA$$

5.82



(a)

$$V_{EQ} = \frac{R_2}{R_2 + R_1} V_{CC} = \frac{36k\Omega}{36k\Omega + 68k\Omega} 10V = 3.462V \quad \left| \begin{array}{l} R_{EQ} = R_2 \parallel R_1 \\ R_{EQ} = 36k\Omega \parallel 68k\Omega = 23.54k\Omega \end{array} \right.$$

$$I_B = \frac{V_{EQ} - V_{BE}}{R_{EQ} + (\beta_F + 1) R_E} \quad \left| \begin{array}{l} I_C = \beta_F I_B \\ I_C = 50 I_B = 80.9 \mu A \end{array} \right. \quad \left| \begin{array}{l} I_E = (\beta_F + 1) I_B \\ I_E = 51 I_B = 82.5 \mu A \end{array} \right.$$

$$I_B = \frac{3.462 - 0.7}{23.54 + (50 + 1) 33k\Omega} V = 1.618 \mu A$$

$$V_{CE} = V_{CC} - R_C I_C - R_E I_E \quad \left| \begin{array}{l} \text{Q-point : } (80.9 \mu A, 3.80 V) \\ I_C \quad V_{CE} \end{array} \right.$$

$$V_{CE} = 10 - 43000 I_C - 33000 I_E = 3.797V$$

(b)

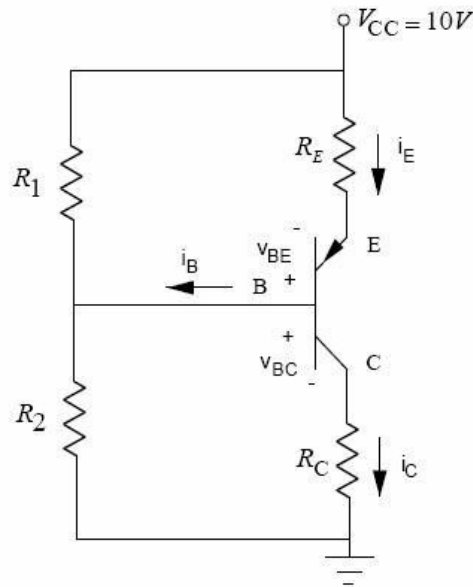
$$R_1 = \frac{68k\Omega}{5} = 13.6k\Omega \quad R_2 = \frac{36k\Omega}{5} = 7.2k\Omega \quad R_E = \frac{33k\Omega}{5} = 6.6k\Omega \quad R_C = \frac{43k\Omega}{5} = 8.6k\Omega$$

$$V_{EQ} = \frac{7.2k\Omega}{7.2k\Omega + 13.6k\Omega} 10V = 3.462V \quad \left| \quad R_{EQ} = 7.2k\Omega \parallel 13.6k\Omega = 4.708k\Omega \right.$$

$$I_B = \frac{3.462 - 0.7}{4.708 + (50 + 1) 6.6k\Omega} V = 8.092 \mu A \quad \left| \quad I_C = 50 I_B = 404.6 \mu A \quad \left| \quad I_E = 51 I_B = 412.7 \mu A \right. \right.$$

$$V_{CE} = 10 - 8600 I_C - 6600 I_E = 3.7976V \quad \left| \quad \text{Q-point : } (405 \mu A, 3.80 V) \right.$$

5.82



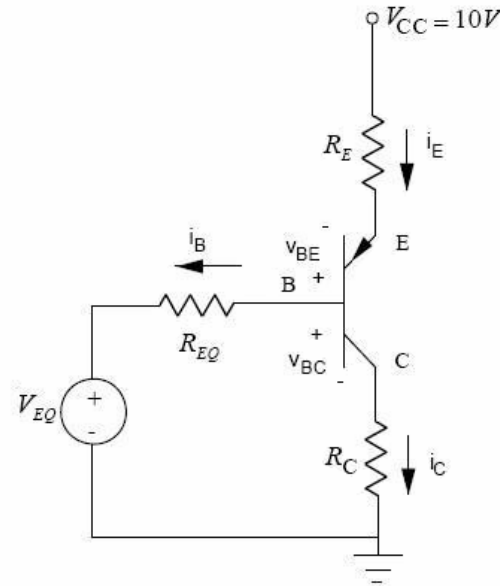
(c)

$$V_{EQ} = \frac{68k\Omega}{36k\Omega + 68k\Omega} 10V = 6.538V \quad | \quad R_{EQ} = 36k\Omega \parallel 68k\Omega = 23.54k\Omega$$

$$I_B = \frac{V_{CC} - V_{EB} - V_{EQ}}{R_{EQ} + (\beta_F + 1)R_E} \quad \left| \quad \begin{array}{l} I_C = \beta_F I_B \\ I_C = 50I_B = 80.9 \mu A \end{array} \right. \quad \left| \quad \begin{array}{l} I_E = (\beta_F + 1)I_B \\ I_E = 51I_B = 82.5 \mu A \end{array} \right.$$

$$I_B = \frac{10 - 0.7 - 6.538}{23.54 + (50 + 1)33} \frac{V}{k\Omega} = 1.618 \mu A$$

$$V_{EC} = 10 - 33000I_C - 43000I_E = 3.797V \quad | \quad \text{Q-point : } (80.9 \mu A, 3.80 V)$$



(d)

$$R_1 = \frac{36k\Omega}{5} = 7.2k\Omega \quad R_2 = \frac{68k\Omega}{5} = 13.6k\Omega \quad R_E = \frac{33k\Omega}{5} = 6.6k\Omega \quad R_C = \frac{43k\Omega}{5} = 8.6k\Omega$$

$$V_{EQ} = \frac{13.6k\Omega}{7.2k\Omega + 13.6k\Omega} 10V = 6.538V \quad | \quad R_{EQ} = 7.2k\Omega \parallel 13.6k\Omega = 4.708k\Omega$$

$$I_B = \frac{10 - 0.7 - 6.538}{4.708 + (50 + 1)6.6} \frac{V}{k\Omega} = 8.092 \mu A \quad | \quad I_C = 50I_B = 404.6 \mu A \quad | \quad I_E = 51I_B = 412.7 \mu A$$

$$V_{EC} = 10 - 6600I_E - 8600I_C = 3.7976V \quad | \quad \text{Q-point : } (405 \mu A, 3.80 V)$$